

DMG90401

Silicon NPN epitaxial planar type (Tr1)
 Silicon PNP epitaxial planar type (Tr2)

For general amplification

■ Features

- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

■ Basic Part Number

DSC2001 + DSA2001 (Individual)

■ Packaging

Embossed type (Thermo-compression sealing): 8000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

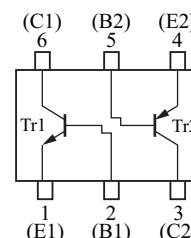
	Parameter	Symbol	Rating	Unit
Tr1	Collector-base voltage (Emitter open)	V_{CBO}	60	V
	Collector-emitter voltage (Base open)	V_{CEO}	50	V
	Emitter-base voltage (Collector open)	V_{EBO}	7	V
	Collector current	I_C	100	mA
	Peak collector current	I_{CP}	200	mA
Tr2	Collector-base voltage (Emitter open)	V_{CBO}	-60	V
	Collector-emitter voltage (Base open)	V_{CEO}	-50	V
	Emitter-base voltage (Collector open)	V_{EBO}	-7	V
	Collector current	I_C	-100	mA
	Peak collector current	I_{CP}	-200	mA
Overall	Total power dissipation	P_T	125	mW
	Junction temperature	T_j	150	$^\circ\text{C}$
	Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Package

- Code
SSMini6-F3-B
- Pin Name
1: Emitter (Tr1) 4: Emitter (Tr2)
2: Base (Tr1) 5: Base (Tr2)
3: Collector (Tr2) 6: Collector (Tr1)

■ Marking Symbol: A9

■ Internal Connection



■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

- Tr1

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = 10 \mu\text{A}, I_E = 0$	60			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = 2 \text{ mA}, I_B = 0$	50			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 10 \mu\text{A}, I_C = 0$	7			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 20 \text{ V}, I_E = 0$			0.1	μA
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = 10 \text{ V}, I_B = 0$			100	μA
Forward current transfer ratio	h_{FE}	$V_{CB} = 10 \text{ V}, I_C = 2 \text{ mA}$	210		460	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$		0.13	0.3	V
Transition frequency	f_T	$V_{CB} = 10 \text{ V}, I_C = 2 \text{ mA}$		150		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		1.5		pF

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

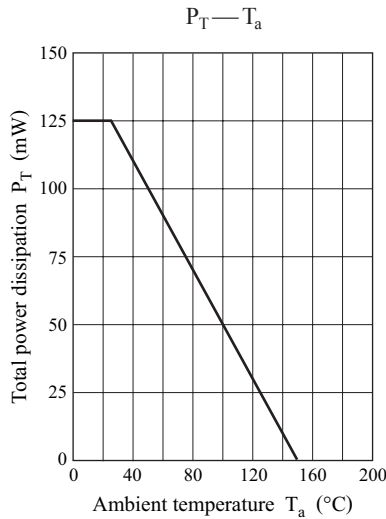
■ Electrical Characteristics (Continued) $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

• Tr2

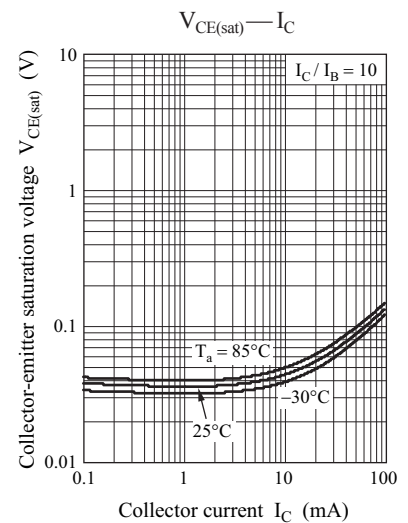
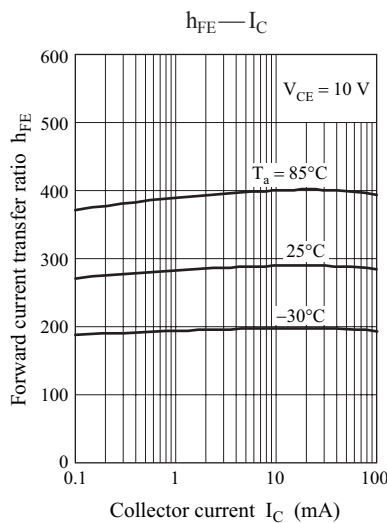
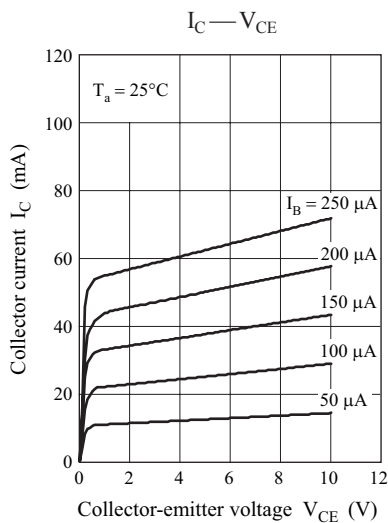
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = -10 \mu\text{A}, I_E = 0$	-60			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = -2 \text{mA}, I_B = 0$	-50			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = -10 \mu\text{A}, I_C = 0$	-7			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -20 \text{V}, I_E = 0$			-0.1	μA
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = -10 \text{V}, I_B = 0$			-100	μA
Forward current transfer ratio	h_{FE}	$V_{CE} = -10 \text{V}, I_C = -2 \text{mA}$	210		460	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100 \text{mA}, I_B = -10 \text{mA}$		-0.2	-0.5	V
Transition frequency	f_T	$V_{CB} = -10 \text{V}, I_C = -2 \text{mA}$		150		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = -10 \text{V}, I_E = 0, f = 1 \text{MHz}$		2		pF

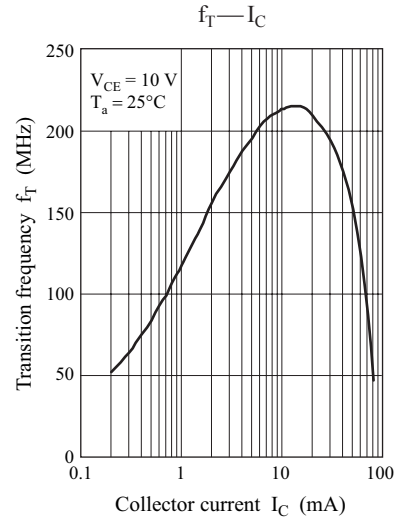
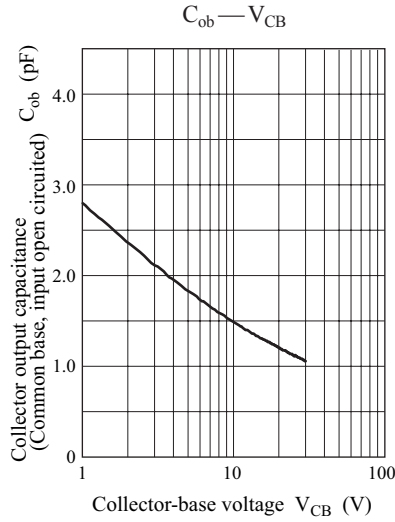
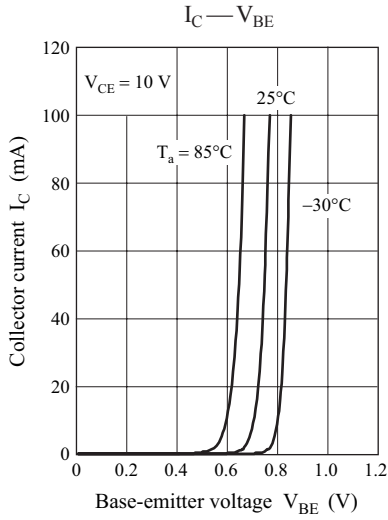
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

Common characteristics chart

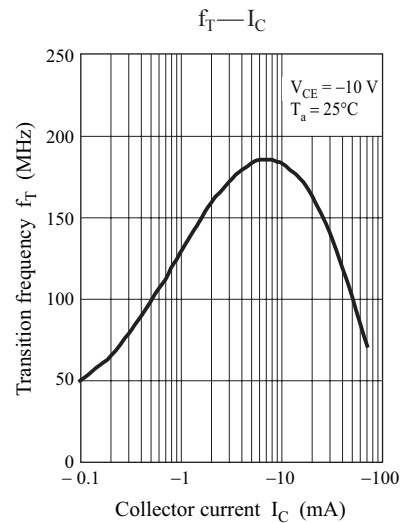
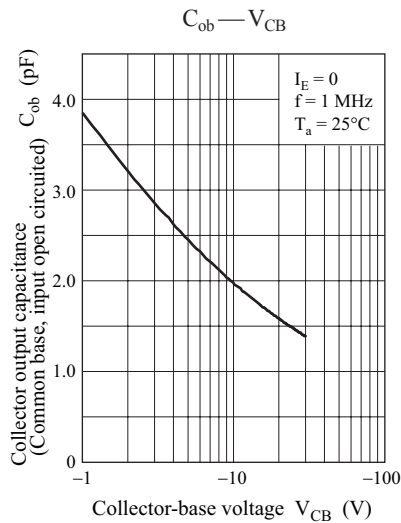
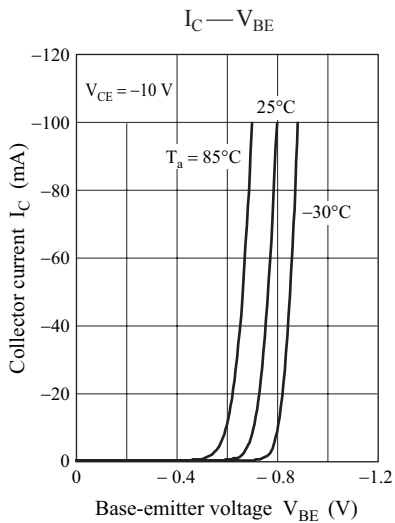
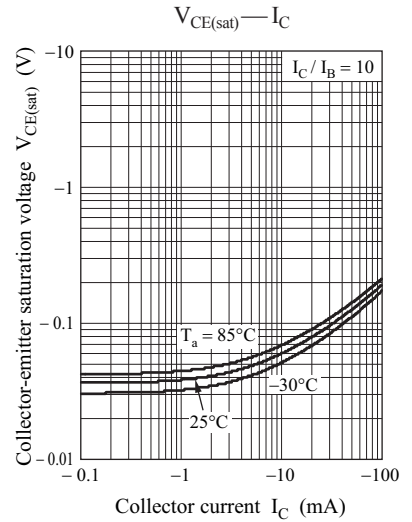
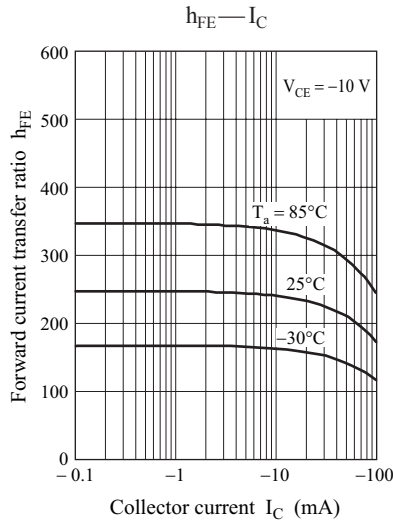
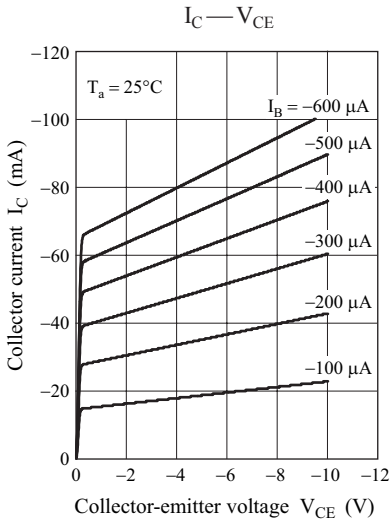


Characteristics charts of Tr1



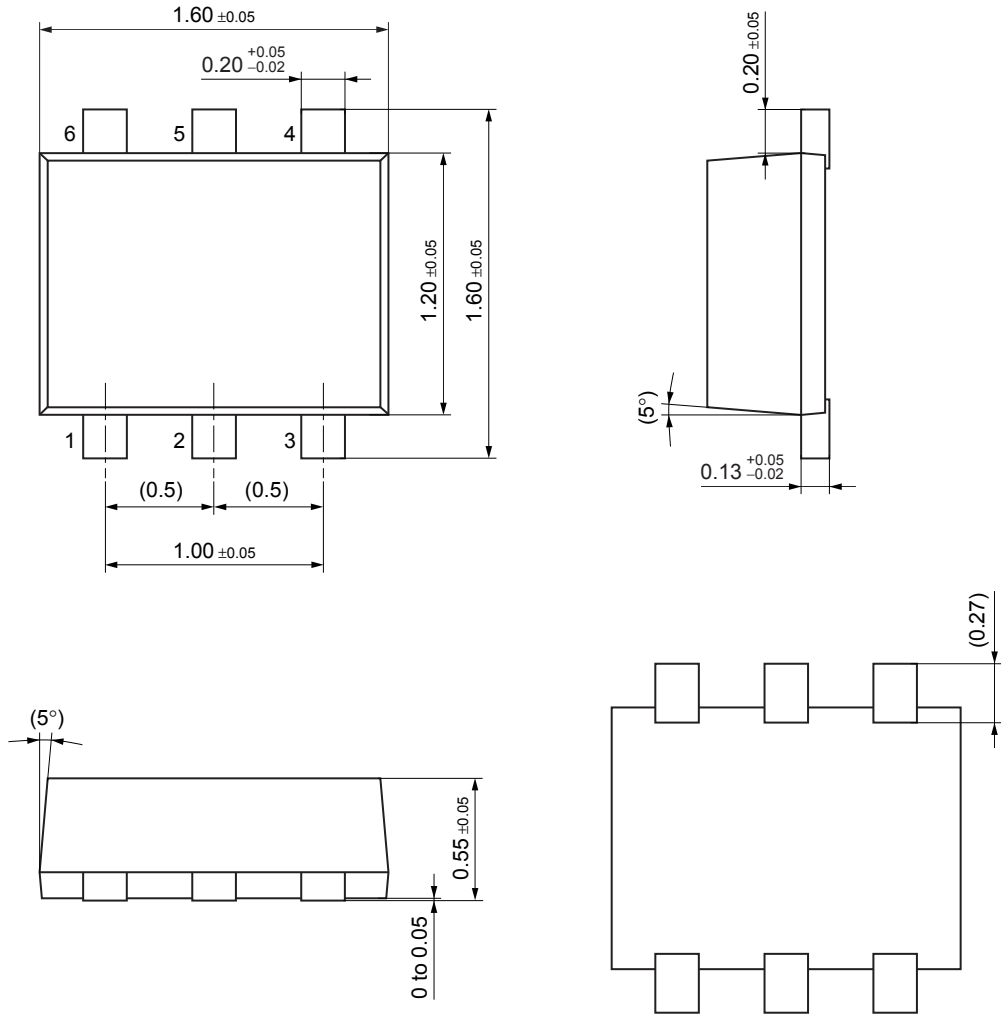


Characteristics charts of Tr2



SSMini6-F3-B

Unit: mm



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